

In the Claims:

No amendments to the claims are presented

1. (Previously presented) A composite substrate comprising
a carrier composed of a carrier material,
a first layer composed of a first material having a dilatation behavior that is
substantially the same as that of the carrier material, and
an intermediate layer composed of a second material being located between the
carrier and the first layer, the second material having a dilatation mismatch with the first
material, the intermediate layer having structures of the second material arranged for
absorbing stress originating from the dilatation mismatch.
2. (Original) A composite substrate according to claim 1, wherein the intermediate
layer has a thickness, and the structures extend through the thickness of the intermediate
layer.
3. (Original) A composite substrate according to claim 1, wherein the structures
further extend into the carrier.
4. (Original) A composite substrate according to claim 1, wherein the carrier
material is the same as the first material.
5. (Previously Presented) A composite substrate according to claim 1, wherein the
carrier material and the first material are semiconductors.
6. (Previously Presented) A composite substrate according to claim 1, wherein the
second material is an electrically insulating material.

7. (Previously Presented) A composite substrate according to claim 1, the intermediate layer lying in a plane, wherein the dimensions of the structures in the plane of the intermediate layer are less than a centimeter.
8. (Previously Presented) A composite substrate according to claim 1, wherein the carrier lies in a plane and wherein the structures have a line-symmetric shape in a cross-section perpendicular to the plane of the carrier.
9. (Previously Presented) A composite substrate according to claim 1, wherein the carrier lies in a plane and wherein the structures have a circular, square, rectangular or rhombic shape in a cross-section parallel to the plane of the carrier.
10. (Previously Presented) A composite substrate according to claim 1, wherein the composite substrate is a silicon-on-insulator wafer.
- 11-20. (Cancelled).
21. (Previously Presented) A composite substrate according to claim 1, wherein the first layer is bonded to the intermediate layer.
22. (Previously Presented) A composite substrate according to claim 1, wherein the second material is composed of an oxide of the carrier material.
23. (Previously Presented) A composite substrate according to claim 1, wherein the structures are formed integrally with the carrier layer.
24. (Previously Presented) A composite substrate according to claim 23, wherein the structures meet the carrier layer at rounded corners.
25. (Previously Presented) A composite substrate according to claim 1, wherein each of the structures has a free surface arranged so that dislocations that form in the structures

due to the stress originating from the dilatation mismatch move to and disappear from the free surface.

26. (Previously Presented) A composite substrate according to claim 1, wherein the structures are included at selected locations of the intermediate layer.

27. (Previously Presented) A composite substrate according to claim 26, wherein the selected locations are where stress originating from the dilatation mismatch is likely to occur.

28. (Previously Presented) A composite substrate according to claim 1, wherein the structures are free standing pillars on the carrier layer.